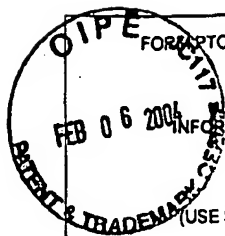


#3IDS
2/6/14



FORMPTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.
MICRON.214DDV1

APPLICATION NO.
10/848,103

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Liu, et al.

FILING DATE
August 22, 2003

GROUP
Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
MSP	6028786		Nishimura			
	6136705		Blair			
	6153443		Durlam, et al.			
	6174737		Durlam, et al.			
	6,218,302		Braeckelmann, et al.			
	6338899		Fukuzawa, et al.			
	6358756		Sandhu, et al.			
	6379978		Goebel, et al.			
	6391658		Gates, et al.			
	2002 / 0041514 A1		Scheler			
MSP	6,440,753		Ning, et al			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

L:\DOCS\MSO\MSO-5307.DOC
013004

EXAMINER

DATE CONSIDERED

12/8/14

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609, DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

COPY

#2 IDS
8/22/3

SHEET 1 OF 2

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.

MICRON 2140V1
21400V1

APPLICATION NO.

10,037,162

Unknown

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT

Liu et al.

FILING DATE

January 24, 2002 Herewith

GROUP

Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
MDP	3,623,032	11/23/71	Schapira			
	3,623,035	11/23/71	Kobayashi et al.			
	3,816,909	6/18/74	Maeda et al.			
	3,947,831	3/30/76	Kobayashi et al.			
	4,044,330	8/23/77	Johnson et al.			
	4,060,794	11/29/77	Feldman et al.			
	4,158,891	6/19/79	Fisher			
	4,455,626	6/19/84	Lutes			
	4,731,757	3/15/88	Daughton et al.			
	4,780,848	10/25/88	Daughton et al.			
	4,801,883	01/31/89	Muller et al.			
	4,849,695	07/18/89	Muller et al.			
	4,945,397	07/31/90	Schuetz			
	5,039,655	8/13/91	Pisharody			
	5,064,499	11/12/91	Fryer			
	5,140,549	8/18/92	Fryer			
	5,496,759	3/5/96	Yue et al.			
	5,547,599	8/20/96	Wolfrey et al.			
	5,569,617	10/29/98	Yeh et al.			
	5,587,943	12/24/98	Torok et al.			
	5,650,958	7/22/97	Gallagher et al.			
	5,701,222	12/23/97	Gill et al.			
	5,726,498	03/10/98	Licata et al.			
	5,741,435	4/21/98	Beetz, Jr. et al.			
	5,756,366	3/28/98	Berg et al.			
MDP	5,795,823	08/18/98	Avanzino et al.			

EXAMINER

DATE CONSIDERED

12/8/4

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

COPY

SHEET 2 OF 2

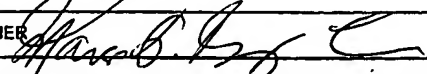
FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON 2148V1 214 PDU1	APPLICATION NO. 40/057,162 Unknown
	APPLICANT Liu et al.	
	FILING DATE January 24, 2002 Herein	GROUP Unknown

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
MDP	5,861,328	1/89	Tehrani et al.			
↓	5,926,394	07/20/99	Nguyen et al.			09/30/96
↓	5,956,267	8/21/99	Hurst et al.			
↓	5,982,658	11/09/99	Berg et al.			
MDP	6,048,739	4/11/00	Hurst et al.			

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
MDP	DE 198 38 567 A 1	2/24/00	Germany				
↓	WO 00/19440	4/8/00	PCT				
↓	EP 0 776 011 A2	5/28/97	EPO				
↓	WO 98/20496	5/14/98	EPO				
MDP	2000-30222	1/2000	Japan				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
MDP	Honeywell Brochure entitled Pohm et al., "The Architecture of a High Performance Mass Store with GMR Memory Cells," <u>Nonvolatile Electronics</u> , pp. 1-3.
↓	Pohm et al., "Experimental and Analytical Properties of 0.2 Micron Wide, Multi-Layer, GMR, Memory Elements," <u>IEEE Transactions on Magnetics</u> , Vol. 32, No. 5, September 1996, pp. 4645-4647.
↓	Prinz, Gary, "Magnetoelectronics," <u>Science</u> , Vol. 282, November 27, 1998, pp. 1660-1663.
↓	Wang, Zhi G. et al., "Feasibility of Ultra-Dense Spin-Tunneling Random Access Memory," <u>IEEE Transactions on Magnetics</u> , Vol. 33, No. 6, November 1997, pp. 4498-4512.
MDP	Razavi et al., "Design Techniques for High-Speed, High-Resolution Comparators", <u>IEEE Journal of Solid State Circuit</u> , Vol. 27, No. 12, December 1992

W:\DOCSUP\FJPF-1091.DOC
021902

EXAMINER 	DATE CONSIDERED 12/8/04
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	